

Jerzy Kanicki

List of Publications by Year in descending order

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307
papers

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46918

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311
docs citations

311
times ranked

4638
citing authors

#	ARTICLE	IF	CITATIONS
1	Bias-stress-induced stretched-exponential time dependence of charge injection and trapping in amorphous thin-film transistors. Applied Physics Letters, 1993, 62, 1286-1288.	1.5	437
2	Thin-Film Organic Polymer Phototransistors. IEEE Transactions on Electron Devices, 2004, 51, 877-885.	1.6	280
3	Two-dimensional numerical simulation of radio frequency sputter amorphous In-Ga-Zn-O thin-film transistors. Journal of Applied Physics, 2009, 106, .	1.1	224
4	Electrically active point defects in amorphous silicon nitride: An illumination and charge injection study. Journal of Applied Physics, 1988, 64, 3558-3563.	1.1	167
5	Density of States of a-InGaZnO From Temperature-Dependent Field-Effect Studies. IEEE Transactions on Electron Devices, 2009, 56, 1177-1183.	1.6	153
6	Performance of thin hydrogenated amorphous silicon thin-film transistors. Journal of Applied Physics, 1991, 69, 2339-2345.	1.1	129
7	Gate dielectric and contact effects in hydrogenated amorphous silicon-silicon nitride thin-film transistors. Journal of Applied Physics, 1989, 65, 3951-3957.	1.1	123
8	High performance organic polymer light-emitting heterostructure devices. Applied Physics Letters, 1999, 74, 2265-2267.	1.5	122
9	Electrical Instability of Hydrogenated Amorphous Silicon Thin-Film Transistors for Active-Matrix Liquid-Crystal Displays. Japanese Journal of Applied Physics, 1998, 37, 4704-4710.	0.8	108
10	Structural ordering and enhanced carrier mobility in organic polymer thin film transistors. Synthetic Metals, 2004, 146, 181-185.	2.1	107
11	Paramagnetic Point Defects in Amorphous Silicon Dioxide and Amorphous Silicon Nitride Thin Films: II .. Journal of the Electrochemical Society, 1992, 139, 880-889.	1.3	105
12	High-efficiency organic polymer light-emitting heterostructure devices on flexible plastic substrates. Applied Physics Letters, 2000, 76, 661-663.	1.5	103
13	Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O Thin-Film Transistors. Journal of Display Technology, 2009, 5, 452-461.	1.3	100
14	Electron paramagnetic resonance investigation of charge trapping centers in amorphous silicon nitride films. Journal of Applied Physics, 1993, 74, 4034-4046.	1.1	98
15	Improved a-Si:H TFT pixel electrode circuits for active-matrix organic light emitting displays. IEEE Transactions on Electron Devices, 2001, 48, 1322-1325.	1.6	93
16	Photofield-effect in amorphous In-Ga-Zn-O (a-IGZO) thin-film transistors. Journal of Information Display, 2008, 9, 21-29.	2.1	92
17	Nature of the dominant deep trap in amorphous silicon nitride. Physical Review B, 1988, 38, 8226-8229.	1.1	88
18	Top-Gate Staggered Amorphous Silicon Thin-Film Transistors: Series Resistance and Nitride Thickness Effects. Japanese Journal of Applied Physics, 1998, 37, 5914-5920.	0.8	84

#	ARTICLE	IF	CITATIONS
19	Field-effect mobility of polycrystalline tetrabenzoporphyrin thin-film transistors. Journal of Applied Physics, 2005, 98, 014503.	1.1	84
20	Current-source a-Si:H thin-film transistor circuit for active-matrix organic light-emitting displays. IEEE Electron Device Letters, 2000, 21, 590-592.	2.2	83
21	Organic Polymer Thin-Film Transistor Photosensors. IEEE Journal of Selected Topics in Quantum Electronics, 2004, 10, 840-848.	1.9	78
22	Bias stress-induced instabilities in amorphous silicon nitride/hydrogenated amorphous silicon structures: Is the "carrier-induced defect creation" model correct?. Applied Physics Letters, 1990, 57, 1197-1199.	1.5	77
23	Structural identification of the silicon and nitrogen dangling bond centers in amorphous silicon nitride. Journal of Applied Physics, 1991, 70, 346-354.	1.1	75
24	Si and N dangling bond creation in silicon nitride thin films. Applied Physics Letters, 1993, 63, 2685-2687.	1.5	73
25	Electrical Properties and Stability of Dual-Gate Coplanar Homo Junction DC Sputtered Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors and Its Application to AM-OLEDs. IEEE Transactions on Electron Devices, 2011, 58, 4344-4353.	1.6	73
26	Ultraviolet light induced changes in polyimide liquid crystal alignment films. Journal of Applied Physics, 1996, 80, 5028-5034.	1.1	72
27	Influence of the Amorphous Silicon Thickness on Top Gate Thin-Film Transistor Electrical Performances. Japanese Journal of Applied Physics, 2001, 40, 530-537.	0.8	71
28	Low frequency noise in long channel amorphous In-Ga-Zn-O thin film transistors. Journal of Applied Physics, 2010, 108, .	1.1	71
29	The nature of the dominant deep trap in amorphous silicon nitride films: Evidence for a negative correlation energy. Applied Surface Science, 1989, 39, 392-405.	3.1	65
30	Stable photoinduced paramagnetic defects in hydrogenated amorphous silicon nitride. Applied Physics Letters, 1987, 51, 608-610.	1.5	62
31	Solution-processed nickel tetrabenzoporphyrin thin-film transistors. Journal of Applied Physics, 2006, 100, 034502.	1.1	61
32	Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. Journal of Applied Physics, 2014, 116, .	1.1	61
33	Four-Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays. Japanese Journal of Applied Physics, 2001, 40, 1199-1208.	0.8	60
34	Far UV pulsed laser melting of silicon. Applied Physics Letters, 1985, 46, 547-549.	1.5	56
35	Microscopic origin of the light-induced defects in hydrogenated nitrogen-rich amorphous silicon nitride films. Journal of Non-Crystalline Solids, 1991, 137-138, 291-294.	1.5	55
36	High-resolution organic polymer light-emitting pixels fabricated by imprinting technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2877.	1.6	55

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37	Pâ€³13: Photosensitivity of Amorphous IGZO TFTs for Activeâ€³Matrix Flatâ€³Panel Displays. Digest of Technical Papers SID International Symposium, 2008, 39, 1215-1218.	0.1	54
38	Electronâ€³spinâ€³resonance study of defects in plasmaâ€³enhanced chemical vapor deposited silicon nitride. Applied Physics Letters, 1988, 52, 445-447.	1.5	53
39	High-Fidelity Electronic Display of Digital Radiographs. Radiographics, 1999, 19, 1653-1669.	1.4	53
40	Solution-processed polycrystalline copper tetrabenzoporphyrin thin-film transistors. Synthetic Metals, 2007, 157, 190-197.	2.1	53
41	Amorphous Inâ€³Gaâ€³Znâ€³O Dual-Gate TFTs: Currentâ€³Voltage Characteristics and Electrical Stress Instabilities. IEEE Transactions on Electron Devices, 2012, 59, 1928-1935.	1.6	53
42	Evidence for a negative electronâ€³electron correlation energy in the dominant deep trapping center in silicon nitride films. Applied Physics Letters, 1990, 56, 1359-1361.	1.5	52
43	Contact resistance to undoped and phosphorusâ€³doped hydrogenated amorphous silicon films. Applied Physics Letters, 1988, 53, 1943-1945.	1.5	51
44	Stability of electrical properties of nitrogenâ€³rich, siliconâ€³rich, and stoichiometric silicon nitride films. Journal of Applied Physics, 1989, 66, 2765-2767.	1.1	51
45	Electrically neutral nitrogen danglingâ€³bond defects in amorphous hydrogenated silicon nitride thin films. Journal of Applied Physics, 1991, 70, 2220-2225.	1.1	50
46	Synthesis and Characterization of Conjugated, n-Dopable, Bithiazole-Containing Polymers. Chemistry of Materials, 1998, 10, 1713-1719.	3.2	50
47	Observation of multiple silicon dangling bond configurations in silicon nitride. Applied Physics Letters, 1989, 54, 1043-1045.	1.5	48
48	Field-Effect Mobility of Organic Polymer Thin-Film Transistors. Chemistry of Materials, 2004, 16, 4699-4704.	3.2	48
49	Thermal annealing of lightâ€³induced metastable defects in hydrogenated amorphous silicon nitride. Applied Physics Letters, 1991, 59, 1723-1725.	1.5	46
50	Amorphous Inâ€³Gaâ€³Znâ€³O thinâ€³film transistor active pixel sensor xâ€³ray imager for digital breast tomosynthesis. Medical Physics, 2014, 41, 091902.	1.6	46
51	Metal - Polyacetylene Schottky Barrier Diodes. Molecular Crystals and Liquid Crystals, 1984, 105, 203-217.	0.4	46
52	Energy level of the nitrogen dangling bond in amorphous silicon nitride. Applied Physics Letters, 1991, 59, 1699-1701.	1.5	45
53	DC sputtered amorphous Inâ€³Snâ€³Znâ€³O thin-film transistors: Electrical properties and stability. Solid-State Electronics, 2016, 116, 22-29.	0.8	45
54	Photobleaching of lightâ€³induced paramagnetic defects in amorphous silicon nitride films. Applied Physics Letters, 1990, 57, 1995-1997.	1.5	44

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55	Nature of the Si and N dangling bonds in silicon nitride. <i>Journal of Non-Crystalline Solids</i> , 1995, 187, 297-300.	1.5	44
56	Patterning of transparent conducting oxide thin films by wet etching for a-Si:H TFT-LCDs. <i>Journal of Electronic Materials</i> , 1996, 25, 1806-1817.	1.0	44
57	Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon Thin-Film Transistor Characteristics. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2251-2255.	0.8	44
58	High field-effect-mobility a-Si:H TFT based on high deposition-rate PECVD materials. <i>IEEE Electron Device Letters</i> , 1996, 17, 437-439.	2.2	43
59	Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization. <i>Medical Physics</i> , 2015, 42, 6294-6308.	1.6	43
60	Investigation of the light-induced effects in nitrogen-rich silicon nitride films. <i>Applied Physics Letters</i> , 1989, 55, 1112-1114.	1.5	42
61	Angular dependence of the luminance and contrast in medical monochrome liquid crystal displays. <i>Medical Physics</i> , 2003, 30, 2602-2613.	1.6	40
62	Gated-four-probe a-Si:H TFT structure: a new technique to measure the intrinsic performance of a-Si:H TFT. <i>IEEE Electron Device Letters</i> , 1997, 18, 340-342.	2.2	39
63	ITO surface ball formation induced by atomic hydrogen in PECVD and HW-CVD tools. <i>Thin Solid Films</i> , 1997, 304, 123-129.	0.8	38
64	Polycrystalline tetrabenzoporphyrin organic field-effect transistors with nanostructured channels. <i>Applied Physics Letters</i> , 2007, 90, 233107.	1.5	38
65	Absolute photoluminescence quantum efficiency measurement of light-emitting thin films. <i>Review of Scientific Instruments</i> , 2007, 78, 096101.	0.6	37
66	Stretched exponential illumination time dependence of positive charge and spin generation in amorphous silicon nitride. <i>Applied Physics Letters</i> , 1990, 57, 698-700.	1.5	36
67	Transparent flexible plastic substrates for organic light-emitting devices. <i>Journal of Electronic Materials</i> , 2004, 33, 312-320.	1.0	36
68	A Novel Current-Scaling a-Si:H TFTs Pixel Electrode Circuit for AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , 2005, 52, 1123-1131.	1.6	36
69	Monte Carlo analysis of the spectral photon emission and extraction efficiency of organic light-emitting devices. <i>Journal of Applied Physics</i> , 2001, 90, 1827-1830.	1.1	35
70	Oxygen flow effects on electrical properties, stability, and density of states of amorphous In ₂ Ga ₂ Zn ₂ O thin-film transistors. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 121101.	0.8	29
71	Charge trapping centers in N-rich silicon nitride thin films. <i>Applied Physics Letters</i> , 1992, 61, 216-218.	1.5	28
72	InGaZnO thin-film transistors for AMOLEDs: Electrical stability and pixel-circuit simulation. <i>Journal of the Society for Information Display</i> , 2009, 17, 525-534.	0.8	28

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73	Creation and Properties of Nitrogen Dangling Bond Defects in Silicon Nitride Thin Films. Journal of the Electrochemical Society, 1996, 143, 3685-3691.	1.3	27
74	Top illuminated organic photodetectors with dielectric/metal/dielectric transparent anode. Organic Electronics, 2015, 20, 103-111.	1.4	27
75	500 nm pixel pitch wafer-scale CMOS active pixel sensor x-ray detector for digital breast tomosynthesis. Physics in Medicine and Biology, 2015, 60, 8977-9001.	1.6	27
76	Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology. Materials Research Society Symposia Proceedings, 1989, 149, 239.	0.1	26
77	Asymmetric Electrical Properties of Corbino a-Si:H TFT and Concepts of Its Application to Flat Panel Displays. IEEE Transactions on Electron Devices, 2007, 54, 654-662.	1.6	26
78	An a-InGaZnO TFT Pixel Circuit Compensating Threshold Voltage and Mobility Variations in AMOLEDs. Journal of Display Technology, 2014, 10, 402-406.	1.3	26
79	Investigation of intrinsic channel characteristics of hydrogenated amorphous silicon thin-film transistors by gated-four-probe structure. Applied Physics Letters, 1998, 72, 2874-2876.	1.5	25
80	Planarized copper gate hydrogenated amorphous-silicon thin-film transistors for AM-LCDs. IEEE Electron Device Letters, 1999, 20, 129-131.	2.2	25
81	Electrical Properties of Staggered Electrode, Solution-Processed, Polycrystalline Tetrabenzoporphyrin Field-Effect Transistors. IEEE Transactions on Electron Devices, 2005, 52, 1497-1503.	1.6	25
82	Amorphous InGaZnO Thin Film Transistor Current-Scaling Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. Japanese Journal of Applied Physics, 2009, 48, 03B025.	0.8	25
83	Tuning Optical and Electronic Properties of Bithiazole Containing Polymers by N-Methylation. Macromolecules, 1999, 32, 2484-2489.	2.2	24
84	Electrical Instability of Double-Gate a-IGZO TFTs With Metal Source/Drain Recessed Electrodes. IEEE Transactions on Electron Devices, 2014, 61, 1109-1115.	1.6	24
85	Dynamic Response of a-InGaZnO and Amorphous Silicon Thin-Film Transistors for Ultra-High Definition Active-Matrix Liquid Crystal Displays. Journal of Display Technology, 2015, 11, 471-479.	1.3	24
86	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. Japanese Journal of Applied Physics, 2011, 50, 091102.	0.8	24
87	Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon thin film Transistors. Materials Research Society Symposia Proceedings, 1988, 118, 267.	0.1	23
88	Short channel amorphous InGaZnO thin-film transistor arrays for ultra-high definition active matrix liquid crystal displays: Electrical properties and stability. Solid-State Electronics, 2015, 111, 67-75.	0.8	23
89	Photodarkening and bleaching in amorphous silicon nitride. Applied Physics Letters, 1990, 57, 1378-1380.	1.5	22
90	Ultraviolet-light Induced Liquid-Crystal Alignment on Polyimide Films. Japanese Journal of Applied Physics, 1999, 38, 5996-6004.	0.8	22

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91	Advanced Amorphous Silicon Thin-Film Transistors for AM-OLEDs: Electrical Performance and Stability. IEEE Transactions on Electron Devices, 2008, 55, 1621-1629.	1.6	22
92	A maskless laser-write lithography processing of thin-film transistors on a hemispherical surface. Microelectronic Engineering, 2010, 87, 83-87.	1.1	22
93	Properties of Electrodeposited WO ₃ Thin Films. Molecular Crystals and Liquid Crystals, 2014, 604, 71-83.	0.4	22
94	Photovoltaic properties of the poly-2-vinylpyridine iodine complexâ€”SnO ₂ system. Journal of Applied Polymer Science, 1982, 27, 1-9.	1.3	21
95	Current-Scaling a-Si:H TFT Pixel-Electrode Circuit for AM-OLEDs: Electrical Properties and Stability. IEEE Transactions on Electron Devices, 2007, 54, 2403-2410.	1.6	21
96	Analyte selective response in solution-deposited tetrabenzoporphyrin thin-film field-effect transistor sensors. Sensors and Actuators B: Chemical, 2011, 158, 333-339.	4.0	21
97	Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques. Materials Research Society Symposia Proceedings, 1988, 118, 671.	0.1	20
98	Defects in amorphous hydrogenated silicon nitride films. Journal of Non-Crystalline Solids, 1993, 164-166, 1055-1060.	1.5	20
99	Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides For a-Si:H TFT-LCDs. Materials Research Society Symposia Proceedings, 1996, 424, 347.	0.1	20
100	Light output measurements of the organic light-emitting devices. Review of Scientific Instruments, 2000, 71, 2104-2107.	0.6	20
101	Spatial charge distribution in the plasma-enhanced chemical vapor deposited nitrogen-rich silicon nitride. Applied Physics Letters, 1989, 54, 733-735.	1.5	19
102	Paramagnetic point defects in silicon nitride and silicon oxynitride thin films on silicon. Colloids and Surfaces A: Physicochemical and Engineering Aspects, 1996, 115, 311-317.	2.3	19
103	Asymmetric electrical properties of fork a-Si:H thin-film transistor and its application to flat panel displays. Journal of Applied Physics, 2009, 105, .	1.1	19
104	Electrochromic device with Prussian blue and HPC-based electrolyte. Electrochimica Acta, 2015, 182, 878-883.	2.6	19
105	Modeling of currentâ€”voltage characteristics for double-gate a-IGZO TFTs and its application to AMLCDs. Journal of the Society for Information Display, 2012, 20, 237-244.	0.8	18
106	Bilayer Interdiffused Heterojunction Organic Photodiodes Fabricated by Double Transfer Stamping. Advanced Optical Materials, 2017, 5, 1600784.	3.6	18
107	Novel Top-Anode OLED/a-IGZO TFTs Pixel Circuit for 8K4K AM-OLEDs. IEEE Transactions on Electron Devices, 2019, 66, 436-444.	1.6	17
108	Direct observation of the silicon nitride on amorphous silicon interface states. Applied Physics Letters, 1990, 56, 940-942.	1.5	16

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109	Observation of incident angle dependent phonon absorption in hydrogenated amorphous silicon nitride thin films. Applied Physics Letters, 1998, 73, 3866-3868.	1.5	16
110	P-11: DC/AC Electrical Instability of R.F. Sputter Amorphous In-Ga-Zn-O TFTs. Digest of Technical Papers SID International Symposium, 2009, 40, 1117.	0.1	16
111	Half-Corbino short-channel amorphous InGaZnO thin-film transistors with a-SiO _x or a-SiO _x /a-SiN _x passivation layers. Solid-State Electronics, 2016, 120, 25-31.	0.8	16
112	Some electrical properties of amorphous silicon/amorphous silicon nitride interfaces: Top nitride and bottom nitride configurations in MNS and TFT devices. Journal of Applied Physics, 1992, 71, 5022-5032.	1.1	15
113	Ultraviolet light induced annihilation of silicon dangling bonds in hydrogenated amorphous silicon nitride films. Journal of Applied Physics, 1995, 77, 5730-5735.	1.1	15
114	Electrical characteristics of new LDD poly-Si TFT structure tolerant to process misalignment. IEEE Electron Device Letters, 1999, 20, 335-337.	2.2	15
115	Interference fringe-free transmission spectroscopy of amorphous thin films. Journal of Applied Physics, 2000, 88, 5764-5771.	1.1	15
116	Opto-Electronic Properties of Poly (Fluorene) Co-Polymer Red Light-Emitting Devices on Flexible Plastic Substrate. IEEE Transactions on Electron Devices, 2004, 51, 1562-1569.	1.6	15
117	P4: AM-OLED Pixel Circuits Based on InGaZnO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2009, 40, 1128-1131.	0.1	15
118	Two-Dimensional Numerical Simulation of Bottom-Gate and Dual-Gate Amorphous In-Ga-Zn-O MESFETs. IEEE Electron Device Letters, 2014, 35, 75-77.	2.2	15
119	Amorphous InSnZnO Thin-Film Transistor Voltage-Mode Active Pixel Sensor Circuits for Indirect X-Ray Imagers. IEEE Transactions on Electron Devices, 2016, 63, 4802-4810.	1.6	15
120	Characterization and stability of light-emitting diodes based on poly(bithiazole)'s. IEEE Transactions on Electron Devices, 1997, 44, 1282-1288.	1.6	14
121	Influence of gate dielectrics on electrical properties of F8T2 polyfluorene thin film transistors. , 2003, , .		14
122	Hexagonal a-Si:H TFTs: A New Advanced Technology for Flat-Panel Displays. IEEE Transactions on Electron Devices, 2008, 55, 329-336.	1.6	14
123	Dynamic Response of Normal and Corbino a-Si:H TFTs for AM-OLEDs. IEEE Transactions on Electron Devices, 2008, 55, 2338-2347.	1.6	14
124	Surface potential study of amorphous InGaZnO thin film transistors. Journal of Applied Physics, 2010, 108, 114508.	1.1	14
125	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. Japanese Journal of Applied Physics, 2011, 50, 091102.	0.8	14
126	Solution-processed zinc tetrabenzoporphyrin thin-films and transistors. Thin Solid Films, 2012, 520, 4031-4035.	0.8	14

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127	High Efficiency Cu(In,Ga)Se ₂ Flexible Solar Cells Fabricated by Roll-to-Roll Metallic Precursor Co-sputtering Method. Japanese Journal of Applied Physics, 2013, 52, 092302.	0.8	14
128	Electrical conductivity and infrared absorption of trans- polyacetylene in the presence of iodine. Journal of the Chemical Society, Faraday Transactions 2, 1981, 77, 2157-2168.	1.1	13
129	Spatial charge distribution in as-deposited and UV-illuminated gate-quality nitrogen-rich silicon nitride. IEEE Electron Device Letters, 1989, 10, 277-279.	2.2	13
130	Enhanced electro-optic effect in amorphous hydrogenated silicon based waveguides. Applied Physics Letters, 1992, 61, 1664-1666.	1.5	13
131	Investigations on the quality of polysilicon film-gate dielectric interface in polysilicon thin film transistors. Thin Solid Films, 1992, 216, 137-141.	0.8	13
132	P-103: Novel Poly-Si TFT Pixel Electrode Circuits and Current Programmed Active-Matrix Driving Methods for AM-OLEDs. Digest of Technical Papers SID International Symposium, 2002, 33, 618.	0.1	13
133	Accurate small-spot luminance measurements. Displays, 2002, 23, 177-182.	2.0	13
134	Integrating sphere charge coupled device-based measurement method for organic light-emitting devices. Review of Scientific Instruments, 2003, 74, 3572-3575.	0.6	13
135	Methanofullerene-coated tetrabenzoporphyrin organic field-effect transistors. Applied Physics Letters, 2005, 87, 173506.	1.5	13
136	Novel Current-Scaling Current-Mirror Hydrogenated Amorphous Silicon Thin-Film Transistor Pixel Electrode Circuit with Cascade Capacitor for Active-Matrix Organic Light-Emitting Devices. Japanese Journal of Applied Physics, 2007, 46, 1343-1349.	0.8	13
137	Advanced Multilayer Amorphous Silicon Thin-Film Transistor Structure: Film Thickness Effect on Its Electrical Performance and Contact Resistance. Japanese Journal of Applied Physics, 2008, 47, 3362-3367.	0.8	13
138	Gellan gum-chitosan-bis(2-aminopropyl)-polyethylene glycol hydrogel for controlled fertilizer release. Journal of Applied Polymer Science, 2018, 135, 45636.	1.3	13
139	Electrical and photovoltaic properties of trans-polyacetylene. Journal Physics D: Applied Physics, 1984, 17, 805-817.	1.3	12
140	Direct determination of the quadratic electro-optic coefficient in an a-Si:H based waveguide. Journal of Non-Crystalline Solids, 1996, 198-200, 107-110.	1.5	12
141	Selective deposition of polycrystalline silicon thin films at low temperature by hot-wire chemical vapor deposition. Applied Physics Letters, 1996, 68, 2681-2683.	1.5	12
142	Optoelectrical properties of four amorphous silicon thin-film transistors 200 dpi active-matrix organic polymer light-emitting display. Applied Physics Letters, 2003, 83, 3233-3235.	1.5	12
143	Structural ordering in F8T2 polyfluorene thin film transistors. , 2003, 5217, 35.		12
144	Monte Carlo Modeling of the Light Transport in Polymer Light-Emitting Devices on Plastic Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2004, 10, 37-44.	1.9	12

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145	100 dpi 4-a-Si:H TFTs Active-Matrix Organic Polymer Light-Emitting Display. IEEE Journal of Selected Topics in Quantum Electronics, 2004, 10, 16-25.	1.9	12
146	Poly(fluorene-oxadiazole) copolymer-based light-emitting devices on a plastic substrate. Synthetic Metals, 2005, 155, 1-10.	2.1	12
147	Study of ionically conducting nanocomposites for reflective electrochromic devices. Electrochimica Acta, 2019, 301, 174-182.	2.6	12
148	Ohmic and Quasi-Ohmic Contacts to Hydrogenated Amorphous Silicon Thin Films. Materials Research Society Symposia Proceedings, 1986, 70, 379.	0.1	11
149	Light-induced effects in hydrogenated amorphous nitrogen-rich silicon nitride films. Journal of Non-Crystalline Solids, 1989, 114, 612-614.	1.5	11
150	Schottky-contact gated-four-probe a-Si:H TFT structure: a new structure to investigate the electrical instability of a-Si:H TFT. IEEE Electron Device Letters, 1998, 19, 382-384.	2.2	11
151	Gate-planarized organic polymer thin film transistors. Journal of Electronic Materials, 2002, 31, 512-519.	1.0	11
152	Influence of DNA and DNA-PEDOT: PSS on dye sensitized solar cell performance. Molecular Crystals and Liquid Crystals, 2016, 627, 38-48.	0.4	11
153	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at $R = 2$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 913-916.	2.2	11
154	Electrical and photovoltaic properties of metal contacts to trans-polyacetylene. Thin Solid Films, 1984, 113, 1-14.	0.8	10
155	Effect of Gate Dielectric on Performance of Polysilicon thin Film Transistors. Materials Research Society Symposia Proceedings, 1990, 182, 357.	0.1	10
156	Thin film transistors in low temperature as-deposited and reduced-crystallization-time polysilicon on 665Å°C strain point glass substrates. Thin Solid Films, 1999, 338, 281-285.	0.8	10
157	White LED based on polyfluorene Co-polymers blend on plastic substrate. IEEE Transactions on Electron Devices, 2006, 53, 427-434.	1.6	10
158	Junction formation between undoped polyacetylene and metals. European Polymer Journal, 1980, 16, 677-678.	2.6	9
159	Photovoltaic and rectification properties of In/trans-(CH) _x /electrodag +502 schottky-barrier cells. Molecular Crystals and Liquid Crystals, 1982, 83, 319-327.	0.9	9
160	Chemical and Mechanical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems. Materials Research Society Symposia Proceedings, 1986, 68, 167.	0.1	9
161	Photoluminescence in Nitrogen-Rich a-SiN _x :H. Materials Research Society Symposia Proceedings, 1992, 258, 661.	0.1	9
162	Temperature dependence of the electron-spin resonance in nitrogen-rich amorphous silicon nitride. Physical Review B, 1994, 49, 13420-13422.	1.1	9

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163	Influence Of The Density of States and Series Resistance on the Field-Effect Activation Energy in a-Si:H TFT. Materials Research Society Symposia Proceedings, 1996, 424, 77.	0.1	9
164	Effect of secondary radiations on the performance of digital radiographic detectors. , 1998, , .		9
165	<title>Planarization technology of a-Si:H TFTs for AM LCDs</title>. , 1998, 3421, 170.		9
166	Amorphous silicon TFT-based active-matrix organic polymer LEDs. IEEE Electron Device Letters, 2003, 24, 451-453.	2.2	9
167	Monte Carlo modeling of organic polymer light-emitting devices on flexible plastic substrates. , 2003, 4800, 156.		9
168	Hydrogenated Amorphous Silicon Thin-Film Transistors. , 2003, , .		9
169	Novel a-Si:H TFT pixel circuit for electrically stable top-anode light-emitting AMOLEDs. Journal of the Society for Information Display, 2007, 15, 545-551.	0.8	9
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